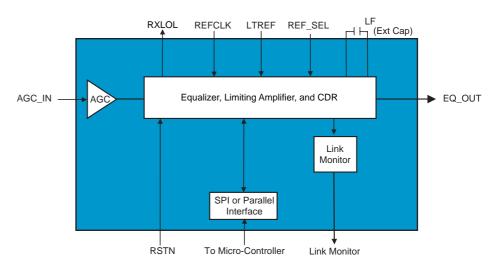


FE	ATURES:	BENEFITS:
▶ N	Multitap FFE and DFE filter	<ul> <li>Provides superior modal dispersion compensation a 10GBASE-LRM specifications</li> </ul>
▶ Ir	ntegrated CDR and XFI output driver	▶ Provides XFP-compatible Rx CDR for XPF LRM mo
▶ Ir	ntegrated AGC and offset controls	Provides robust handing of wide TIA input signal rar conditions

# FUNCTIONAL BLOCK DIAGRAM:



## APPLICATIONS:

1=====

- ▶ XENPAK/X2 10GBASE-LRM module applications
- ▶ XFP 10GBASE-LRM module applications

equalization (FFE) and decision feedback equalization (DFE) architecture. The device is

designed to operate at 10.3125 Gbps for use in 10GBASE-LRM Ethernet applications. The receive chain within the VSC8238 device incorporates a low-noise automatic gain-controlled amplifier, a high-speed adaptive

It also provides the adequate performance marginal multimode fiber applications. The VSC8238 deviated market meeting the LX-4 compliant perform transmission up to 300 meters on 99% of the ins

741 Cam

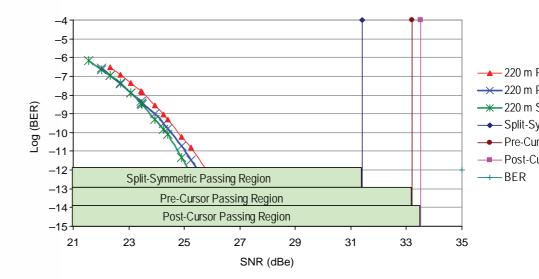
Tel: Fax:

www

sale

## VSC8238 STRESSOR ELECTRICAL PERFORMANCE:

IEEE802.3aq/D3.1 220 m post-cursor, pre-cursor, and split-symmetric stressor performance as a function of log BER versus SNR (nominal conditions, input: ~400 mV differential)



### SPECIFICATIONS:

- Exceeds IEEE 802.3aq Draft 4.0 specifications for 10GBASE-LRM performance
- ▶ Passes the following LRM stressor tests:
  - Split-symmetric 4.75 dB PIE-D stressor (300 m)
  - Post-cursor 4.56 dB PIE-D stressor (300 m)
  - Pre-cursor 4.48 dB PIE-D stressor (300 m)

#### Fradomarks <sup>TM</sup>

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